

## ABSTRACT

The invention relates generally to lithographic patterning of very small features. In particular, the invention relates generally to patterning of semiconductor circuit features smaller than lithographically defined using either conventional optical lithography or next generation lithography techniques. The invention relates more particularly, but not by way of limitation, to lateral trimming of photoresist images.

5

10  
15  
20  
25  
30  
35  
40  
45  
50  
55  
60  
65  
70  
75  
80  
85  
90  
95  
100